Process	$\tau_{\text{lep}}\tau_{\text{lep}}$	$\tau_{\text{lep}}\tau_{\text{had}}$	$\tau_{\text{had}}\tau_{\text{had}}$
$Z \to \ell\ell$-enriched	$80 < m_{\tau\tau}^{\text{vis}} < 100~GeV$ (same-flavour)		
Top control region	Invert b-jet veto	Invert b-jet veto and $m_{\text{T}} > 40~GeV$	
Rest category			Pass preselection, Fail VBF and Boosted selections
$Z \to \tau\tau$-enriched	$m_{\tau\tau}^{\text{HPTO}} < 100~GeV$	$m_{\text{T}} < 40~GeV$ and $m_{\tau\tau}^{\text{MMC}} < 110~GeV$	
Fake-enriched	Same sign τ decay products	Same sign τ decay products	
W-enriched		$m_{\text{T}} > 70~GeV$	
Mass sideband			$m_{\tau\tau}^{\text{MMC}} < 110~GeV$ or $m_{\tau\tau}^{\text{MMC}} > 150~GeV$